

Epi - Wafer

Blue LED



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|---------------------------------------|--|
| Feature | Blue LED Epi. Wafer Single side polished (Growth surface) |
| Diameter | 2" (50.8mm) |
| Thickness (Included substrate) | 430 μ m \pm 15 μ m |
| Structure | p-GaN / MQWs / n-GaN / u-GaN / Sapphire substrate |



GaN on Sapphire Wafer

Characteristics (at 25°C)

| Parameter | | Typ. | Test Conditions |
|-----------------|-----------------------|-----------------------|---|
| PL measurement | Peak wavelength | 450nm \pm 20nm | Accent RPM2000 - Laser : 266nm Nd-YG - 3mm Edge Exclude |
| | Uniformity STD | <3% | |
| | FWHM | <10nm | |
| | FWHM STD | <20% | |
| Thickness | Thickness | 4.8 μ m \pm 10% | |
| | Thickness STD | <10% | |
| XRD | (002) | N/A | Panalytical HRXRD |
| | (102) | N/A | |
| Hall | Carrier Concentration | N/A | Accent HL5500 |
| | Mobility | N/A | |
| Doping material | Si | used | - |
| | Mg | used | |

Normalized Single Spectrum(300 ~ 700nm)

